

# Hideto Miyake

## List of Publications by Year in descending order

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267  
papers

4,935  
citations

136950

32  
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138484

58  
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270  
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270  
docs citations

270  
times ranked

2755  
citing authors

#	ARTICLE	IF	CITATIONS
1	Limits on Astrophysical Antineutrinos with the KamLAND Experiment. <i>Astrophysical Journal</i> , 2022, 925, 14.	4.5	22
2	Search for Solar Flare Neutrinos with the KamLAND Detector. <i>Astrophysical Journal</i> , 2022, 924, 103.	4.5	1
3	Transcriptome analysis of molecular response to UVC irradiation in zebrafish embryos. <i>Ecotoxicology and Environmental Safety</i> , 2022, 231, 113211.	6.0	3
4	Reduction of dislocation density in lattice-relaxed Al <sub>0.68</sub> Ga <sub>0.32</sub> N film grown on periodical 1 $\mu$ m spacing AlN pillar concave-convex patterns and its effect on the performance of UV-B laser diodes. <i>Applied Physics Express</i> , 2022, 15, 031004.	2.4	16
5	Fabrication of vertical AlGaIn-based deep-ultraviolet light-emitting diodes operating at high current density ( $\sim 43$ kA cm <sup>-2</sup> ) using a laser liftoff method. <i>Applied Physics Express</i> , 2022, 15, 041006.	2.4	9
6	A Search for Correlated Low-energy Electron Antineutrinos in KamLAND with Gamma-Ray Bursts. <i>Astrophysical Journal</i> , 2022, 927, 69.	4.5	2
7	Centimeter-scale laser lift-off of an AlGaIn UVB laser diode structure grown on nano-patterned AlN. <i>Applied Physics Express</i> , 2022, 15, 051004.	2.4	9
8	Impacts of Si-doping on vacancy complex formation and their influences on deep ultraviolet luminescence dynamics in Al <sub>x</sub> Ga <sub>1-x</sub> N films and multiple quantum wells grown by metalorganic vapor phase epitaxy. <i>Japanese Journal of Applied Physics</i> , 2022, 61, 050501.	1.5	4
9	Thermal radiation resonating with longitudinal optical phonon from surface micro-stripe structures on metal-gallium nitride and sapphire. <i>Materials Science in Semiconductor Processing</i> , 2022, 147, 106726.	4.0	6
10	Rare UV-resistant cells in clonal populations of Escherichia coli. <i>Journal of Photochemistry and Photobiology B: Biology</i> , 2022, 231, 112448.	3.8	1
11	High-Quality AlN Template Prepared by Face-to-Face Annealing of Sputtered AlN on Sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2000352.	1.5	16
12	High-quality AlN/sapphire templates prepared by thermal cycle annealing for high-performance ultraviolet light-emitting diodes. <i>Applied Physics Express</i> , 2021, 14, 035505.	2.4	26
13	Search for Low-energy Electron Antineutrinos in KamLAND Associated with Gravitational Wave Events. <i>Astrophysical Journal</i> , 2021, 909, 116.	4.5	12
14	AlGaIn Channel High Electron Mobility Transistors with Regrown Ohmic Contacts. <i>Electronics (Switzerland)</i> , 2021, 10, 635.	3.1	27
15	AlGaIn-based UV-B laser diode with a high optical confinement factor. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	36
16	Analysis of carrier injection efficiency of AlGaIn UV-B laser diodes based on the relationship between threshold current density and cavity length. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 074002.	1.5	10
17	High Electron Mobility AlN on Sapphire (0001) with a Low Dislocation Density Prepared via Sputtering and High-Temperature Annealing. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2100074.	1.8	2
18	Thick AlN layers grown on micro-scale patterned sapphire substrates with sputter-deposited annealed AlN films by hydride vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 2021, 566-567, 126163.	1.5	6

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19	Effect of the Sputtering Deposition Conditions on the Crystallinity of High-Temperature Annealed AlN Films. <i>Coatings</i> , 2021, 11, 956.	2.6	8
20	The nylon balloon for xenon loaded liquid scintillator in KamLAND-Zen 800 neutrinoless double-beta decay search experiment. <i>Journal of Instrumentation</i> , 2021, 16, P08023.	1.2	11
21	Thermal strain analysis considering in-plane anisotropy for sputtered AlN on <i>c</i> - and <i>a</i> -plane sapphire under high-temperature annealing. <i>AIP Advances</i> , 2021, 11, .	1.3	3
22	Effect of MOVPE growth conditions on AlN films on annealed sputtered AlN templates with nano-stripped patterns. <i>Journal of Crystal Growth</i> , 2021, 570, 126237.	1.5	2
23	Low-threshold-current (~85 mA) of AlGaIn-based UV-B laser diode with refractive-index waveguide structure. <i>Applied Physics Express</i> , 2021, 14, 094009.	2.4	14
24	Reduction of threading dislocation densities of N-polar face-to-face annealed sputtered AlN on sapphire. <i>Journal of Crystal Growth</i> , 2021, 574, 126309.	1.5	12
25	Reduction of dislocation density in Al <sub>0.6</sub> Ga <sub>0.4</sub> N film grown on sapphire substrates using annealed sputtered AlN templates and its effect on UV-B laser diodes. <i>Journal of Crystal Growth</i> , 2021, 575, 126325.	1.5	12
26	Fabrication of AlN templates by high-temperature face-to-face annealing for deep UV LEDs. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 120502.	1.5	14
27	AlGaIn-based UV-B laser diode fabricated on AlN with 1 μm periodic concave and convex patterns. , 2021, , .		0
28	Extremely high internal quantum efficiency of AlGaIn-based quantum wells on face-to-face annealed sputter-deposited AlN templates. <i>Applied Physics Express</i> , 2021, 14, 122004.	2.4	6
29	High-temperature Annealing of Sputter-deposited AlN on (001) Diamond Substrate. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900447.	1.5	2
30	MOVPE growth of AlN films on nano-patterned sapphire substrates with annealed sputtered AlN. <i>Journal of Crystal Growth</i> , 2020, 532, 125397.	1.5	17
31	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	24
32	Crystalline quality improvement of face-to-face annealed MOVPE-grown AlN on vicinal sapphire substrate with sputtered nucleation layer. <i>Journal of Crystal Growth</i> , 2020, 545, 125722.	1.5	10
33	Effect of dislocation density on optical gain and internal loss of AlGaIn-based ultraviolet-B band lasers. <i>Applied Physics Express</i> , 2020, 13, 045504.	2.4	17
34	Room-temperature operation of AlGaIn ultraviolet-B laser diode at 298 nm on lattice-relaxed Al <sub>0.6</sub> Ga <sub>0.4</sub> N/AlN/sapphire. <i>Applied Physics Express</i> , 2020, 13, 031004.	2.4	72
35	Internal loss of AlGaIn-based ultraviolet-B band laser diodes with p-type AlGaIn cladding layer using polarization doping. <i>Applied Physics Express</i> , 2020, 13, 071008.	2.4	34
36	Suppression of dislocation-induced spiral hillocks in MOVPE-grown AlGaIn on face-to-face annealed sputter-deposited AlN template. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	44

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37	High Crystallinity and Highly Relaxed Al <sub>0.60</sub> Ga <sub>0.40</sub> N Films Using Growth Mode Control Fabricated on a Sputtered AlN Template with High-Temperature Annealing. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900868.	1.8	16
38	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. Photonics Research, 2020, 8, 610.	7.0	8
39	Low dislocation density AlN on sapphire prepared by double sputtering and annealing. Applied Physics Express, 2020, 13, 095501.	2.4	32
40	Statistics of excitonic energy states based on phononic-excitonic-radiative model. Japanese Journal of Applied Physics, 2019, 58, SCCB34.	1.5	4
41	Structural analysis of polarity inversion boundary in sputtered AlN films annealed under high temperatures. Japanese Journal of Applied Physics, 2019, 58, SCCB30.	1.5	13
42	Reduction of threading dislocation density and suppression of cracking in sputter-deposited AlN templates annealed at high temperatures. Applied Physics Express, 2019, 12, 065501.	2.4	59
43	Ultraviolet-B band lasers fabricated on highly relaxed thick Al <sub>0.55</sub> Ga <sub>0.45</sub> N films grown on various types of AlN wafers. Japanese Journal of Applied Physics, 2019, 58, SC1052.	1.5	36
44	Local and anisotropic strain in AlN film on sapphire observed by Raman scattering spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SCCB17.	1.5	11
45	Improved emission intensity of UVC-LEDs from using strain relaxation layer on sputter-annealed AlN. Japanese Journal of Applied Physics, 2019, 58, SCCC07.	1.5	6
46	Preparation of high-quality thick AlN layer on nanopatterned sapphire substrates with sputter-deposited annealed AlN film by hydride vapor-phase epitaxy. Japanese Journal of Applied Physics, 2019, 58, SC1003.	1.5	15
47	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. Advanced Optical Materials, 2019, 7, 1801763.	7.3	43
48	Curvature-controllable and crack-free AlN/sapphire templates fabricated by sputtering and high-temperature annealing. Journal of Crystal Growth, 2019, 512, 131-135.	1.5	9
49	Quantitative evaluation of strain relaxation in annealed sputter-deposited AlN film. Journal of Crystal Growth, 2019, 512, 16-19.	1.5	27
50	Impact of face-to-face annealed sputtered AlN on the optical properties of AlGaIn multiple quantum wells. AIP Advances, 2019, 9, 125342.	1.3	18
51	Fabrication of AlN templates on SiC substrates by sputtering-deposition and high-temperature annealing. Journal of Crystal Growth, 2019, 510, 13-17.	1.5	12
52	Polarity inversion of aluminum nitride by direct wafer bonding. Applied Physics Express, 2018, 11, 031003.	2.4	14
53	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al <sub>0.61</sub> Ga <sub>0.39</sub> N Epitaxial Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700374.	1.5	4
54	AlGaIn-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. Applied Physics Letters, 2018, 112, .	3.3	171

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55	Microstructural analysis in the depth direction of a heteroepitaxial AlN thick film grown on a trench-patterned template by nanobeam X-ray diffraction. Journal of Applied Physics, 2018, 123, .	2.5	3
56	Growth of High-Quality AlN and AlGa <sub>N</sub> Films on Sputtered AlN/Sapphire Templates via High-Temperature Annealing. Physica Status Solidi (B): Basic Research, 2018, 255, 1700506.	1.5	30
57	Growth of Si-doped AlN on sapphire (0001) via pulsed sputtering. APL Materials, 2018, 6, .	5.1	7
58	Improvement mechanism of sputtered AlN films by high-temperature annealing. Journal of Crystal Growth, 2018, 502, 41-44.	1.5	76
59	Temperature dependence of excitonic transitions in Al <sub>0.60</sub> Ga <sub>0.40</sub> N/Al <sub>0.70</sub> Ga <sub>0.30</sub> N multiple quantum wells from 4 to 750 K. Journal of Applied Physics, 2018, 123, .	2.5	4
60	Selective area growth of GaN on trench-patterned nonpolar bulk GaN substrates. Journal of Crystal Growth, 2017, 468, 851-855.	1.5	1
61	A design strategy for achieving more than 90% of the overlap integral of electron and hole wavefunctions in high-AlN-mole-fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells. Applied Physics Express, 2017, 10, 015802.	2.4	13
62	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al <sub>0.60</sub> Ga <sub>0.40</sub> N/Al <sub>0.70</sub> Ga <sub>0.30</sub> N multiple quantum wells. Applied Physics Express, 2017, 10, 021002.	2.4	8
63	Confinement-enhanced biexciton binding energy in AlGa <sub>N</sub> -based quantum wells. Applied Physics Express, 2017, 10, 051003.	2.4	2
64	High-quality and highly-transparent AlN template on annealed sputter-deposited AlN buffer layer for deep ultra-violet light-emitting diodes. AIP Advances, 2017, 7, 055110.	1.3	45
65	Structural study of GaN grown on nonpolar bulk GaN substrates with trench patterns. Japanese Journal of Applied Physics, 2017, 56, 125504.	1.5	1
66	Fabrication of high-crystallinity a-plane AlN films grown on r-plane sapphire substrates by modulating buffer-layer growth temperature and thermal annealing conditions. Journal of Crystal Growth, 2017, 468, 845-850.	1.5	23
67	Fabrication and characterization of a binary diffractive lens for controlling the focal length and depth of focus. , 2017, , .		0
68	Microscopic potential fluctuations in Si-doped AlGa <sub>N</sub> epitaxial layers with various AlN molar fractions and Si concentrations. Journal of Applied Physics, 2016, 119, .	2.5	5
69	Preparation of high-quality AlN on sapphire by high-temperature face-to-face annealing. Journal of Crystal Growth, 2016, 456, 155-159.	1.5	231
70	Annealing of an AlN buffer layer in N <sub>2</sub> /CO for growth of a high-quality AlN film on sapphire. Applied Physics Express, 2016, 9, 025501.	2.4	166
71	Microstructural analysis of an epitaxial AlN thick film/trench-patterned template by three-dimensional reciprocal lattice space mapping technique. Applied Physics Express, 2016, 9, 111001.	2.4	6
72	Impact of high-temperature annealing of AlN layer on sapphire and its thermodynamic principle. Japanese Journal of Applied Physics, 2016, 55, 05FL02.	1.5	48

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73	Excitation and deexcitation dynamics of excitons in a GaN film based on the analysis of radiation from high-order states. Journal Physics D: Applied Physics, 2016, 49, 245102.	2.8	4
74	Reduction of dislocation density of aluminium nitride buffer layer grown on sapphire substrate. Journal of Mechanical Engineering and Sciences, 2016, 10, 1908-1916.	0.6	3
75	Reduction in the concentration of cation vacancies by proper Si-doping in the well layers of high AlN mole fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2015, 107, 121602.	3.3	27
76	Spatio-time-resolved cathodoluminescence studies on the Si-doping effects in high AlN mole fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells grown on an AlN template by metalorganic vapor phase epitaxy. , 2015, , .		0
77	Fabrication of AlGa <sub>N</sub> multiple quantum wells on sapphire with lattice-relaxation layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 361-364.	0.8	0
78	Growth Characteristics of Graphene Film by Chemical Vapor Deposition Method Using Nozzle Gas Injection. E-Journal of Surface Science and Nanotechnology, 2015, 13, 265-268.	0.4	0
79	Study on AlN growth conditions for hydride vapor phase epitaxy. Transactions of the Materials Research Society of Japan, 2015, 40, 395-396.	0.2	0
80	Excitation-dependent carrier dynamics in Al-rich AlGa <sub>N</sub> layers and multiple quantum wells. Physica Status Solidi (B): Basic Research, 2015, 252, 1043-1049.	1.5	6
81	Extraordinary Optical Transmission Exhibited by Surface Plasmon Polaritons in a Double-Layer Wire Grid Polarizer. Plasmonics, 2015, 10, 1657-1662.	3.4	19
82	Detection of high-refractive index media by a surface plasmon sensor using a one-dimensional metal diffraction grating. , 2015, , .		0
83	Growth and characterization of Cu <sub>2</sub> ZnSn(S <sub>1-x</sub> Se <sub>x</sub> ) <sub>4</sub> single crystal grown by traveling heater method. Journal of Crystal Growth, 2015, 423, 9-15.	1.5	11
84	Solution growth of chalcopyrite compounds single crystal. Renewable Energy, 2015, 79, 127-130.	8.9	9
85	HVPE homoepitaxy on freestanding AlN substrate with trench pattern. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 334-337.	0.8	6
86	Using surface-plasmon polariton at the GaP-Au interface in order to detect chemical species in high-refractive-index media. Optics Communications, 2015, 341, 64-68.	2.1	13
87	Microscopic crystalline structure of a thick AlN film grown on a trench-patterned AlN/Al <sub>2</sub> O <sub>3</sub> template. Journal of Crystal Growth, 2015, 411, 38-44.	1.5	8
88	Growth of AlN Crystals on SiC Substrates by Thermal Nitridation of Al <sub>2</sub> O <sub>3</sub> . Journal of the American Ceramic Society, 2014, 97, 3781-3786.	3.8	2
89	Inhomogeneous distribution of defect-related emission in Si-doped AlGa <sub>N</sub> epitaxial layers with different Al content and Si concentration. Journal of Applied Physics, 2014, 115, .	2.5	21
90	Crack-free GaN grown by using maskless epitaxial lateral overgrowth on Si substrate with thin SiC intermediate layer. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 744-747.	1.8	3

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91	Binding energy of localized biexcitons in AlGaIn-based quantum wells. Applied Physics Express, 2014, 7, 122101.	2.4	8
92	Anisotropic crystalline morphology of epitaxial thick AlN films grown on triangular-striped AlN/sapphire template. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 731-735.	1.8	3
93	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 765-768.	1.8	9
94	Si concentration dependence of structural inhomogeneities in Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> N/Al <sub>y</sub> Ga <sub>1-y</sub> N multiple quantum well structures (x=0.6) and its relationship with internal quantum efficiency. Journal of Applied Physics, 2014, 116, .	1.5	5
95	Thermo-physical properties of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Journal of Crystal Growth, 2014, 393, 167-170.	1.5	21
96	Growth and characterization of Cu <sub>2</sub> ZnSn(S,Se) <sub>4</sub> alloys grown by the melting method. Journal of Crystal Growth, 2014, 386, 204-207.	1.5	20
97	Properties of GaN grown on Si(111) substrates dependent on the thickness of 3C-SiC intermediate layers. Journal of Applied Physics, 2014, 115, .	2.5	6
98	Effects of sodium on electrical properties in Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Applied Physics Letters, 2014, 104, .	3.3	113
99	Cross-sectional X-ray microdiffraction study of a thick AlN film grown on a trench-patterned AlN/Al <sub>2</sub> O <sub>3</sub> template. Journal of Crystal Growth, 2013, 381, 37-42.	1.5	10
100	Growth and characterization of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1328-1331.	1.8	26
101	Correlation between intrinsic defects and electrical properties in the high-quality Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Applied Physics Letters, 2013, 103, .	3.3	69
102	Study on the effects of AlN interlayer in thick GaN grown on 3C-SiC/Si substrates. Journal of Crystal Growth, 2013, 370, 254-258.	1.5	4
103	The excitation of the surface plasmon polariton with the GaP-Au contact and application to chemical sensors. , 2013, , .		0
104	Nanoindentation hardness and elastic modulus of AlGaIn alloys. , 2013, , .		1
105	Effects of Si doping in high-quality AlN grown by MOVPE on trench-patterned template. Journal of Crystal Growth, 2013, 370, 74-77.	1.5	5
106	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al <sub>0.6</sub> Ga <sub>0.4</sub> N films grown on AlN templates by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2013, 113, .	2.5	98
107	AlN Grown on a- and n-Plane Sapphire Substrates by Low-Pressure Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JB31.	1.5	13
108	Growth and Characterization of AlGaIn Multiple Quantum Wells for Electron-Beam Target for Deep-Ultraviolet Light Sources. Japanese Journal of Applied Physics, 2013, 52, 01AF03.	1.5	28

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109	Photoluminescence due to Inelastic Biexciton Scattering from an Al <sub>0.61</sub> Ga <sub>0.39</sub> N Ternary Alloy Epitaxial Layer at Room Temperature. Applied Physics Express, 2012, 5, 072401.	2.4	8
110	Temperature Dependence of Linear Thermal Expansion of CuGaSe <sub>2</sub> Crystals. Materials Science Forum, 2012, 725, 171-174.	0.3	2
111	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaIn quantum wells. Applied Physics Letters, 2012, 101, 042110.	3.3	45
112	Correlation between in-plane strain and optical polarization of Si-doped AlGaIn epitaxial layers as a function of Al content and Si concentration. Journal of Applied Physics, 2012, 112, 033512.	2.5	8
113	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. Journal of Crystal Growth, 2012, 350, 69-71.	1.5	24
114	Preparation of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals from Sn solutions. Journal of Crystal Growth, 2012, 341, 38-41.	1.5	69
115	Growth of Cu <sub>2</sub> ZnSnSe <sub>4</sub> single crystals from Sn solutions. Journal of Crystal Growth, 2012, 354, 147-151.	1.5	41
116	Native cation vacancies in Si-doped AlGaIn studied by monoenergetic positron beams. Journal of Applied Physics, 2012, 111, .	2.5	53
117	Orientation dependence of polarized Raman spectroscopy for nonpolar, semi-polar, and polar bulk GaN substrates. Applied Physics Letters, 2012, 100, .	3.3	13
118	Interaction of the dual effects triggered by AlN interlayers in thick GaN grown on 3C-SiC/Si substrates. Journal Physics D: Applied Physics, 2012, 45, 385101.	2.8	0
119	Strain control of GaN grown on 3C-SiC/Si substrate using AlGaIn buffer layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 550-553.	0.8	5
120	Effects of carrier gas ratio and growth temperature on MOVPE growth of AlN. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 499-502.	0.8	14
121	Fabrication of crack-free thick AlN film on c-plane sapphire by low-pressure HVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 576-579.	0.8	7
122	Observation of longitudinal-optic-phonon-plasmon-coupled mode in n-type AlGaIn alloy films. Applied Physics Letters, 2011, 99, 251904.	3.3	9
123	HVPE growth of c-plane AlN on a-plane sapphire using nitridation layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 470-472.	0.8	6
124	HVPE growth of AlN on trench-patterned 6H-SiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 467-469.	0.8	11
125	Recombination dynamics of localized excitons in Al <sub>x</sub> Ga <sub>1-x</sub> N (0.37 < x < 0.81) ternary alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2133-2135.	0.8	6
126	Evidence for moving of threading dislocations during the VPE growth in GaN thin layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1487-1490.	0.8	5



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127	HVPE growth of thick AlN on trench-patterned substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1483-1486.	0.8	8
128	Control of AlN buffer/sapphire substrate interface for AlN growth. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2069-2071.	0.8	16
129	Huge binding energy of localized biexcitons in Al-rich Al <sub>x</sub> Ga <sub>1-x</sub> N ternary alloys. <i>Applied Physics Letters</i> , 2011, 98, 081907.	3.3	8
130	Silicon concentration dependence of optical polarization in AlGa <sub>x</sub> N epitaxial layers. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	14
131	Fabrication of Deep-Ultraviolet-Light-Source Tube Using Si-Doped AlGa <sub>x</sub> N. <i>Applied Physics Express</i> , 2011, 4, 042103.	2.4	58
132	Growth of High-Quality Si-Doped AlGa <sub>x</sub> N by Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 095502.	1.5	23
133	Growth of Cu <sub>2</sub> ZnSnS <sub>4</sub> Single Crystal by Traveling Heater Method. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 128001.	1.5	3
134	In-plane structural anisotropy and polarized Raman-active mode studies of nonpolar AlN grown on 6H-SiC by low-pressure hydride vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2010, 312, 490-494.	1.5	10
135	Formation mechanism of Al-depleted bands in MOVPE-AlGa <sub>x</sub> N layer on GaN template with trenches. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 2036-2039.	0.8	0
136	a-plane AlN and AlGa <sub>x</sub> N growth on r-plane sapphire by MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 2107-2110.	0.8	8
137	Variation of Surface Potentials of Si-Doped Al <sub>x</sub> Ga <sub>1-x</sub> N (0) Tj ETQq1 1 0.784314 rgBT /Overload <i>Physics Express</i> , 2010, 3, 021004.	2.4	6
138	Deep Electronic Levels of Al <sub>x</sub> Ga <sub>1-x</sub> N with a Wide Range of Al Composition Grown by Metal-Organic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 101001.	1.5	11
139	In-plane electric field induced by polarization and lateral photovoltaic effect in a-plane GaN. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	8
140	Growth of High Quality c-plane AlN on a-plane Sapphire. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1202, 55.	0.1	1
141	Facet-control in selective area growth (SAG) of a-plane GaN by MOVPE. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1202, 98.	0.1	0
142	Fabrication of a binary diffractive lens for controlling the luminous intensity distribution of LED light. <i>Optical Review</i> , 2009, 16, 455-457.	2.0	8
143	Effects of initial conditions and growth temperature on the properties of nonpolar a-plane AlN grown by LP-HVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S478.	0.8	6
144	Mobility enhancement of 2DEG in MOVPE-grown AlGa <sub>x</sub> N/AlN/GaN HEMT structure using vicinal (0 0 0 1) sapphire. <i>Superlattices and Microstructures</i> , 2009, 46, 812-816.	3.1	13

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